Product data sheet

1. Product profile

1.1 General description

Ultrafast, epitaxial rectifier diode in a SOD59 (TO-220AC) plastic package.

1.2 Features

- Fast switching
- Soft recovery characteristic
- Low forward voltage drop
- Low thermal resistance
- High thermal cycling performance

1.3 Applications

- High frequency switched-mode power supplies
- Discontinuous Current Mode (DCM)Power Factor Correction (PFC)

1.4 Quick reference data

- V_{RRM} ≤ 600 V
- V_F ≤ 1.11 V

- $I_{F(AV)} \leq 9 A$
- $t_{rr} \le 60 \text{ ns}$

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	cathode (k)		. 14
2	anode (a)	mb	k — ↓ a 001aaa020
mb	mounting base; cathode	1 2	
		SOD59 (2-lead TO-220)	AC)



3. Ordering information

Table 2. Ordering information

Type number	Package				
	Name	Description	Version		
BYV29-600	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59		

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

	<u> </u>	<u> </u>			
Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	square waveform; δ = 1.0; $T_{mb} \le 100$ °C	-	600	V
I _{F(AV)}	average forward current	square waveform; δ = 0.5; $T_{mb} \leq$ 120 $^{\circ}C$	-	9	Α
I _{FRM}	repetitive peak forward current	square waveform; δ = 0.5; $T_{mb} \leq$ 120 $^{\circ}C$	-	18	Α
I _{FSM}	non-repetitive peak forward current	t = 10 ms; sinusoidal waveform	-	70	Α
		t = 8.3 ms; sinusoidal waveform	-	77	Α
T _{stg}	storage temperature		-40	+150	°C
Tj	junction temperature		-	150	°C

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound; see Figure 1	-	-	2.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

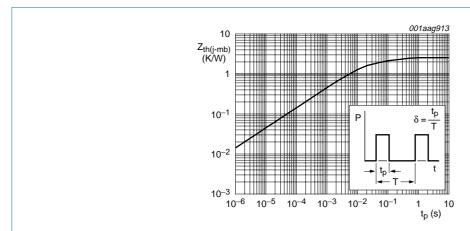


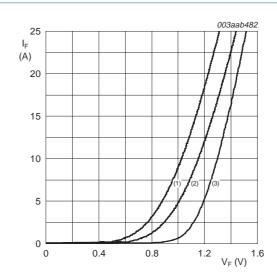
Fig 1. Transient thermal impedance from junction to mounting base as a function of pulse width

6. Characteristics

Table 5. Characteristics

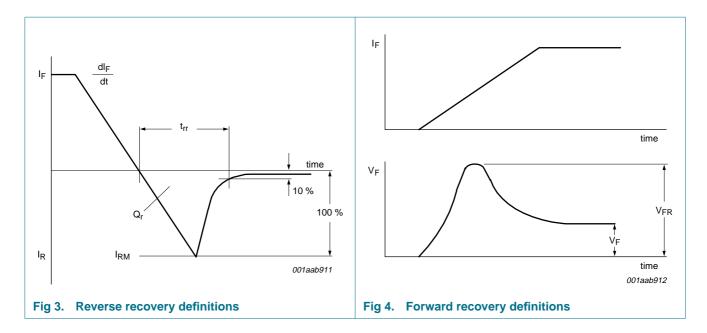
 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _F	forward voltage	$I_F = 8 \text{ A}$; $T_j = 150 ^{\circ}\text{C}$; see Figure 2	-	0.97	1.11	V
		I _F = 8 A	-	1.12	1.25	V
		I _F = 20 A; see Figure 2	-	1.31	1.45	V
I _R	reverse current	V _R = 600 V	-	2	50	μΑ
		$V_R = 600 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	0.1	0.35	mΑ
Dynamic c	haracteristics					
Q _r	recovered charge	I_F = 2 A to V_R \geq 30 V; dI_F/dt = 20 A/ μ s; see Figure 3	-	40	70	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A to V}_R \ge 30 \text{ V};$ $dI_F/dt = 100 \text{ A/}\mu\text{s}; \text{ see } \frac{\text{Figure 3}}{}$	-	50	60	ns
I _{RM}	peak reverse recovery current	I_F = 10 A to V_R \geq 30 V; dI_F/dt = 50 A/ μ s; T_j = 100 °C; see Figure 3	-	3	5.5	Α
V_{FR}	forward recovery voltage	$I_F = 10 \text{ A}$; $dI_F/dt = 10 \text{ A/}\mu\text{s}$; see Figure 4	-	3.2	-	V



- (1) $T_j = 150 \,^{\circ}\text{C}$; typical values
- (2) $T_j = 150 \,^{\circ}\text{C}$; maximum values
- (3) $T_j = 25$ °C; maximum values

Fig 2. Forward current as a function of forward voltage



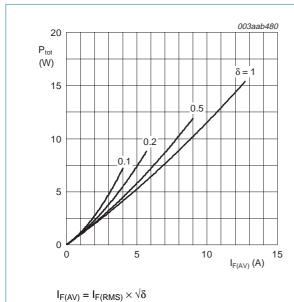


Fig 5. Forward power dissipation as a function of average forward current; square waveform; maximum values

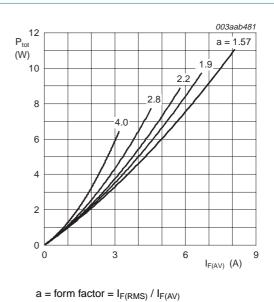


Fig 6. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC

SOD59

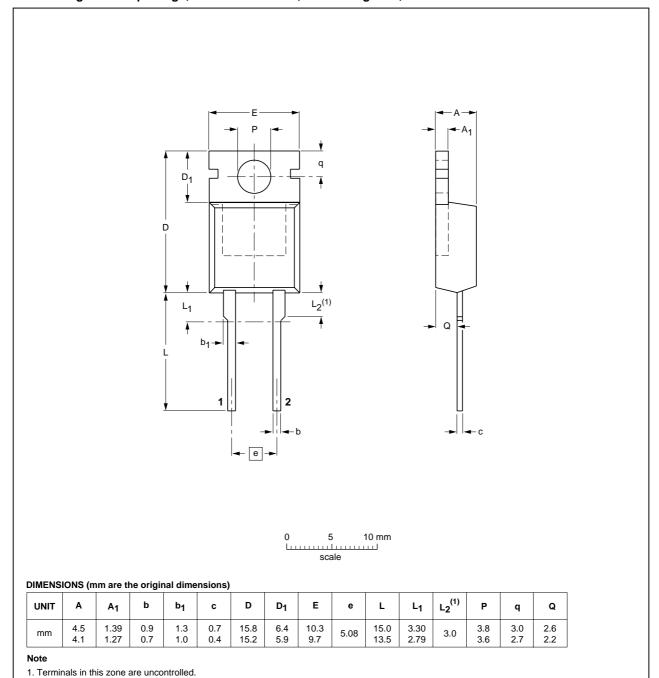


Fig 7. Package outline SOD59 (2-lead TO-220AC)

IEC

JEITA

REFERENCES

JEDEC

2-lead TO-220AC

OUTLINE

VERSION

SOD59

ISSUE DATE

99-09-13

EUROPEAN

PROJECTION

8. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV29-600_2	20071024	Product data sheet	-	BYV29-600_1
Modifications: • The format of this data sheet has been redesigned to comply with the new identity g NXP Semiconductors.				new identity guidelines of
	 Legal texts have 	ave been adapted to the new o	company name where appro	opriate.
	 Table 5 "Char 	racteristics" on page 3: V _F valu	ies updated.	
BYV29-600_1	20000201	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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BYV29-600

Rectifier diode ultrafast

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